

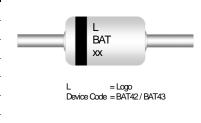
SEMICONDUCTOR

200 mW DO-35 Hermetically Sealed Glass Fast Switching Schottky Barrier Diode



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Power Dissipation	000		
	200	mW	
Storage Temperature Range -65 to +125		°C	
Operating Junction Temperature	+125	°C	
Repetitive Peak Reverse Voltage	30	V	
V _R Maximum DC Blocking Voltage 30		V	
Average Forward Rectified Current	200	mA	
Peak Forward Surge Current	4	Α	
	Operating Junction Temperature Repetitive Peak Reverse Voltage Maximum DC Blocking Voltage Average Forward Rectified Current Peak Forward Surge Current	Operating Junction Temperature +125 Repetitive Peak Reverse Voltage 30 Maximum DC Blocking Voltage 30 Average Forward Rectified Current 200	



DEVICE MARKING DIAGRAM

Specification Features:

- Low Forward Voltage Drop
- DO-35 Package (JEDEC)
- Through-Hole Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All External Surfaces Are Corrosion Resistant And Leads Are Readily Solderable
- RoHS Compliant
- Solder Hot Dip Tin (Sn) Lead Finish

Cathode Anode

ELECTRI CAL SYMBOL

Electrical Characteristics $T_A = 25$ °C unless otherwise noted

Symbol	Power of the state	Test Condition	Limits		l l m l t
	Parameter		Min	Max	Unit
Ву	Breakdown Voltage	I _R =100μA	30		Volts
I _R	Reverse Leakage Current	V _R =25V		500	nA
V _F	Forward Voltage TCBAT42	I _F =10mA		0.40	
		I _F =50mA		0.65	
	TCBAT43	I _F =2mA	0.26	0.33	Volts
		I _F =15mA		0.45	
	TCBAT42, TCBAT43		1.0		
T _{RR}	Reverse Recovery Time	I _F =I _R =10mA			
		R _L =100Ω	5 (Ty	pical)	nS
		I _{RR} =1mA			
С	Capacitance	V _R =1V, f=1M _{HZ}	7 (Ty	pical)	pF

March 2008 / B

These ratings are limiting values above which the serviceability of the diode may be impaired.



SEMICONDUCTOR

Package Outline

Package **Case Outline**

DO-35

	DO-35				
DIM	Millimeters		Inches		
	Min	Max	Min	Max	
Α	0.46	0.55	0.018	0.022	
В	3.05	5.08	0.120	0.200	
С	25.40	38.10	1.000	1.500	
D	1.53	2.28	0.060	0.090	

Notes:

All dimensions are within JEDEC standard.

This datasheet presents technical data of Tak Cheong's Schottky Diode. Complete specifications for the individual devices are provided in the form of datasheets. A comprehensive Selector Guide is included to simplify the task of choosing the best set of components required for a specific application. For additional information, please visit our website http://www.takcheong.com.

Although information in this datasheet has been carefully checked, no responsibility for the inaccuracies can be assumed by Tak Cheong. Please consult your nearest Tak Cheong's sales office for further assistance.

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